

# Hall Effect Single Channel Speed Sensor DSL xx10.0x xxV



## Product ID

	Type #	Product #	Drawing #		
	DSL 1010.00 SHV	378Z-05366	4-113.729A Rev.000		
	DSL 1010.01 SHV	378Z-05367	4-113.731A Rev.000		
	DSL 1010.02 SHV	378Z-05371	4-113.741A Rev.000		
	DSL 1010.03 KHV	378Z-05497	4-114236 Rev. 001		
	DSL 1210.02 A1HV / EEG	56A 3782608661	120605 Rev.000		
	DSL 1210.03 SHV	385Z-05721	115044 Rev.000		
	DSL 1810.01 SHV	378Z-05517	114330 Rev.003		
	DSL EH10.00 AHV	378Z-05806	115446 Rev.004		
	DSL EH10.00 A1HV	378Z-05919	115940 Rev.000		
	DSL EH10.00 A2HV	3742608112	120356 Rev.000		
	DSL EH10.01 AHV	3742606646	117358 Rev.000		
	DSL EH10.02 AHV	3742607887	119351 Rev.001		
General					
Function	The speed sensors DSL are				
	generating square wave signals proportional to rotary speeds. They have a sta				
	behaviour, so that pulse gen	eration is guaranteed of	down to a speed		
	behaviour, so that pulse gen corresponding to a frequency	eration is guaranteed o	down to a speed element is a magnetically		
	behaviour, so that pulse gen corresponding to a frequency biased Hall effect semicondu	eration is guaranteed o of 0 Hz. The sensing otor. The sensor funct	down to a speed element is a magnetically		
	behaviour, so that pulse gen corresponding to a frequency biased Hall effect semicondu rotational orientation of the s	eration is guaranteed o of 0 Hz. The sensing octor. The sensor funct ensor axis.	down to a speed element is a magnetically ion is independent of the		
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Supply voltage	825 VDC
Current consumption	Max. 12 mA (without load)
Signal output	Electronics A: Square wave signal from NPN output transistor with internal 2.7 kΩ pull-up resistor, DC-coupled to supply (negative pole = reference voltage). • Sink current: max. 25 mA • Output voltage: • U <sub>high</sub> ≈ supply voltage • U <sub>low</sub> < 1.0 V at I = 25 mA
	<ul> <li>Electronics B:</li> <li>Square wave signal from NPN output transistor with internal 2.7 kΩ pull-up resistor, DC-coupled to supply (negative pole = reference voltage).</li> <li>Sink current: max. 25 mA</li> <li>Output voltage: <ul> <li>U<sub>high</sub> ≈ supply voltage</li> <li>U<sub>how</sub> &lt; 1.0 V at I = 25 mA</li> </ul> </li> <li>Protected against reverse polarity and overvoltage</li> </ul>
	<ul> <li>Electronics C: Square wave signal from NPN output transistor with internal 2.7 kΩ pull-up resistor and internal 1.0 kΩ pull-down resistor, DC-coupled to supply (negative pole = reference voltage).</li> <li>Sink current: max. 25 mA</li> <li>Output voltage: <ul> <li>Pull-up (560Ω): U<sub>high</sub> ≈ 7.8 V, U<sub>low</sub> ≈ 0.25 V at U<sub>in</sub> = 12V, I = 19 mA</li> <li>Pull-down (560Ω): U<sub>high</sub> ≈ 1.0 V, U<sub>low</sub> ≈ 0 V at U<sub>in</sub> = 12V, I = 5.5 mA</li> </ul> </li> <li>Protected against reverse polarity and overvoltage</li> </ul>
	<ul> <li>Electronics D: Square wave signal from PNP output transistor with internal series diode and series resistor of 330Ω, DC-coupled to supply (negative pole = reference voltage).</li> <li>Source current: max. 25 mA</li> <li>Output voltage: <ul> <li>U<sub>high</sub> &gt; (supply voltage) -2.8V-I*330Ω</li> <li>U<sub>low</sub> ≈ 0V (supply voltage reference) Protected against reverse polarity and overvoltage</li> </ul> </li> <li>Protected against reverse polarity and overvoltage</li> </ul>
Frequency range	0 Hz 15 kHz
Housing	Stainless steel 1.4305, front side sealed hermetically and resistant against splashing water, oil, conducting carbon- or ferrous dust and salt mist. Electronic components potted in chemical and age proof synthetic resin. Dimensions according to drawing.
Requirements for pole wheel	<ul> <li>Toothed wheel of a magnetically permeable material (e.g. Steel 1.0036)</li> <li>Optimal performance with</li> <li>Involute gear</li> <li>Tooth width &gt; 10 mm</li> <li>Side offset &lt; 0.2 mm</li> <li>Eccentricity &lt; 0.2 mm</li> </ul>
Air gap between sensor and pole wheel	<ul> <li>Module 1.0 (DP 25.4): 0.30.5 mm</li> <li>Module 2.0 (DP 12.7): 0.31.5 mm</li> </ul>

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Cable versions	Type #	Cable [Jaquet part no.]	Cable length [mm]		
	DSL 1010.00 SHV	824L-35053	1000		
	DSL 1010.01 SHV	824L-35053	1000		
	DSL 1010.02 SHV	824L-35053	1000		
	DSL 1010.03 KHV	Twisted litz wires:			
		823T-32487 (red)	100		
		823T-32489 (yellow)	100		
		823T-37526 (black)	100		
	DSL 1210.03 SHV	824L-37645	1000		
	DSL 1810.01 SHV	824L-33024	400		
Connector versions	(green), temperature 824L-35053: 0.24 mm <sup>2</sup> ETFE isola (white), temperature 824L-37645: Elastomer cable, 3-v radius min. 50 mm, to Operating temperatu Cable is not in Cable is in mo Twisted litz wires (82 0.22 mm <sup>2</sup> (AWG 24)	unscreened, green ire: motion: -40℃ to +180℃ tion: -25℃ to +180℃ 23T-32487, 823T-32489, 823 Teflon insulated, outer diam	. bending radius 60 mm (metal net), FEP sheating n bending radius. 60 mm ter-Ø max. 4.8 mm, bending 8T-37526):		
Connector versions	Type #	Connector			
	DSL EH10.00 AHV DSL EH10.00 A1HV				
	DSL EH10.00 A2HV				
	DSL EH10.01 AHV				
	DSL EH10.02 AHV				
	DSL 1210.02 A1HV Connector mates with straight plug M12x1, 4 pins				
Insulation	Housing and electronic	s galvanically separated (500	0 V/50 Hz/ 1 min)		
Vibration immunity	30 g in the range 520		·		
Shock immunity	50 g during 20 ms, half	50 g during 20 ms, half-sine wave			
Temperature		of entire sensor: -40° +125	5°C		

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Further Information					
Safety	<ul> <li>All mechanical installations must be carried out by an expert. General safety requirements have to be met.</li> <li>The sensors must be connected according to the sensor drawing. Sensor wires are susceptible to radiated noise. Therefore, the following points have to be considered when connecting a sensor:</li> <li>The sensor wires must be positioned as far as possible from large electrical machines.</li> <li>They must not run in the vicinity of power cables.</li> <li>It is advantageous to keep the distance between sensor and instrument as short as possible. If the signal requirements are met, the sensor cable may be lengthened via a terminal box located in an IP20 connection area in</li> </ul>				
Connection					
Installation	accordance with EN 60529. The sensor has to be aligned to the pole wheel according to the sensor drawing. A deviation in positioning may affect the performance and decrease the noise immunity of the sensor. Within the air gap specified the amplitude of the output signals is not influenced by the air gap. The smallest possible pole wheel to sensor gap should be set, however, the gap should be set to prevent the face of the sensor from touching the pole wheel. The sensor should be positioned such that the center of the sensor face corresponds to the middle of a pole wheel tooth. For larger teeth a misalignment of the sensor center to the middle of a tooth is permissible, however, the center of the sensor must be at a minimum of 3 mm from either edge of the pole wheel under all operating conditions. A solid and vibration free mounting of the sensor is important. Sensor vibration relative to the pole wheel may add spurious noise to the signal. The sensors are insensitive to oil, grease etc. and can be installed in arduous				
Operation	The sensor is designed for normal use in its dedicated environment. The manufacturer cannot take responsibility for any abnormal use that might lead to a reduced lifetime of the sensor.				
Maintenance	Product cannot be repaired.				
Transport	Product must be handled with care to prevent damage of the front face.				
Storage	Product must be stored in dry conditions. The storage temperature corresponds to the operation temperature.				
Disposal	Product must be disposed of properly, it must not be disposed as domestic waste.				

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